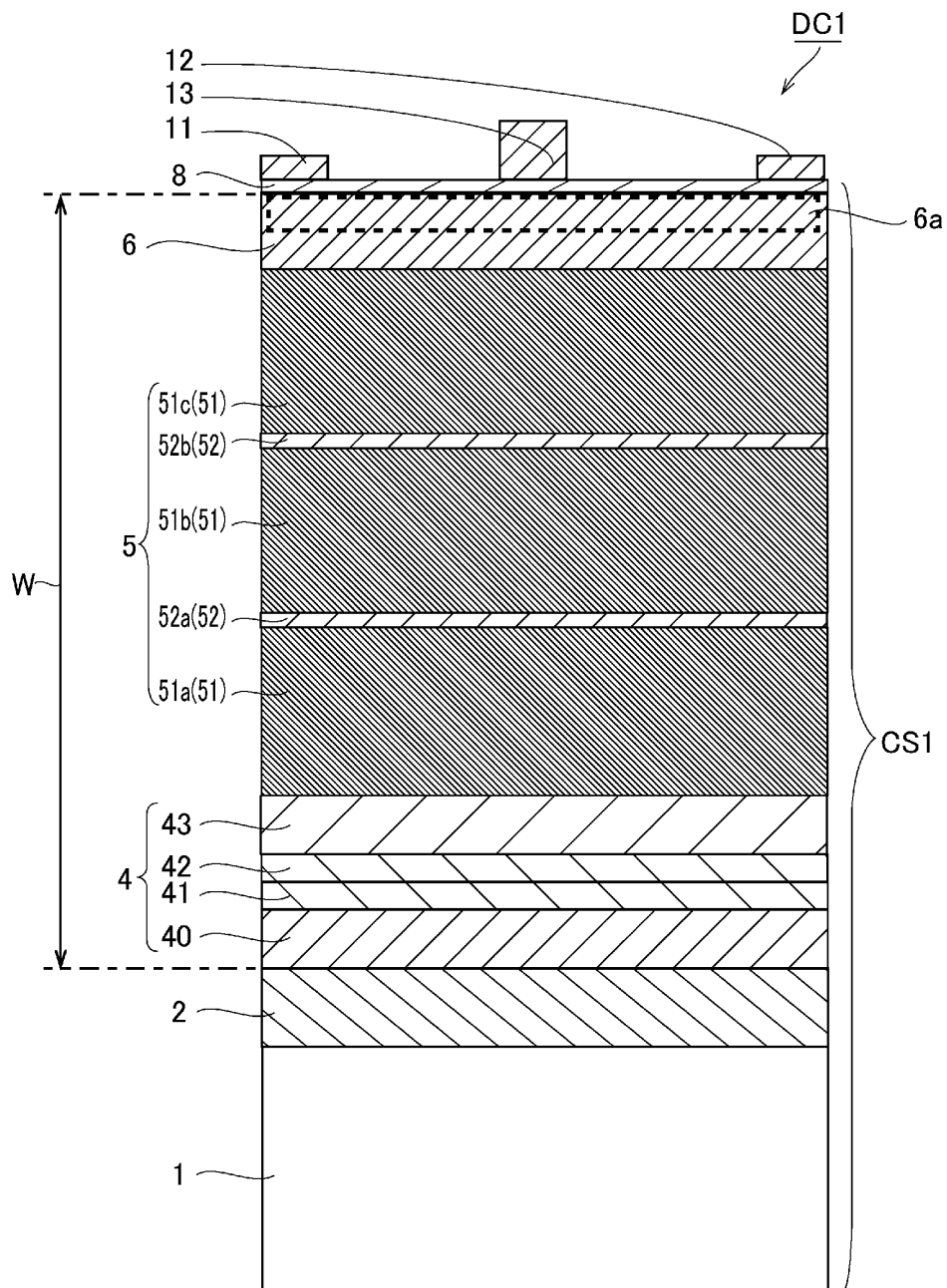
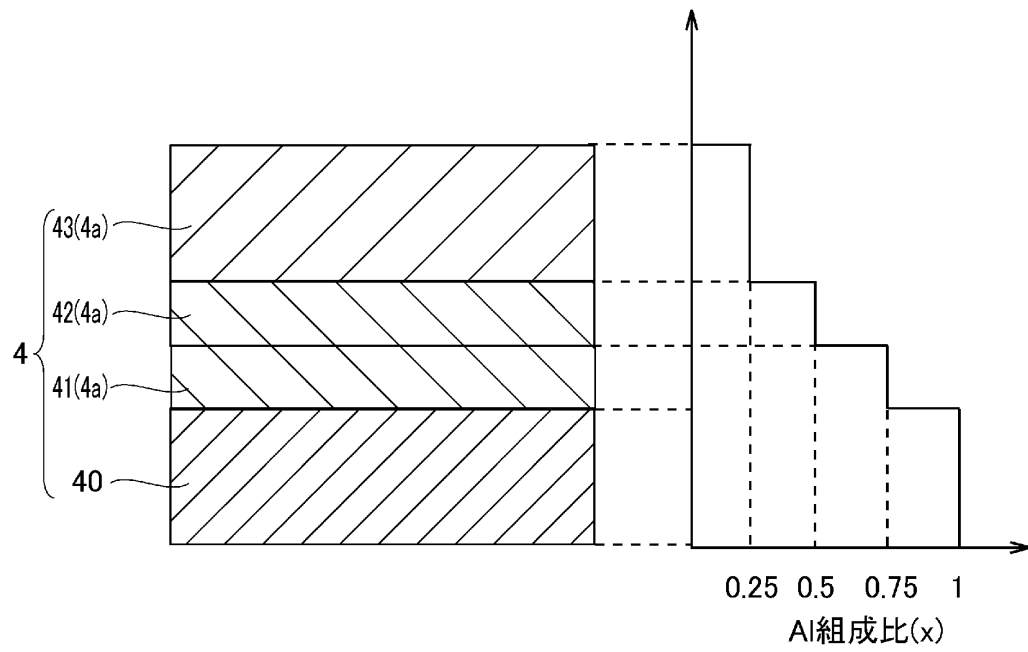


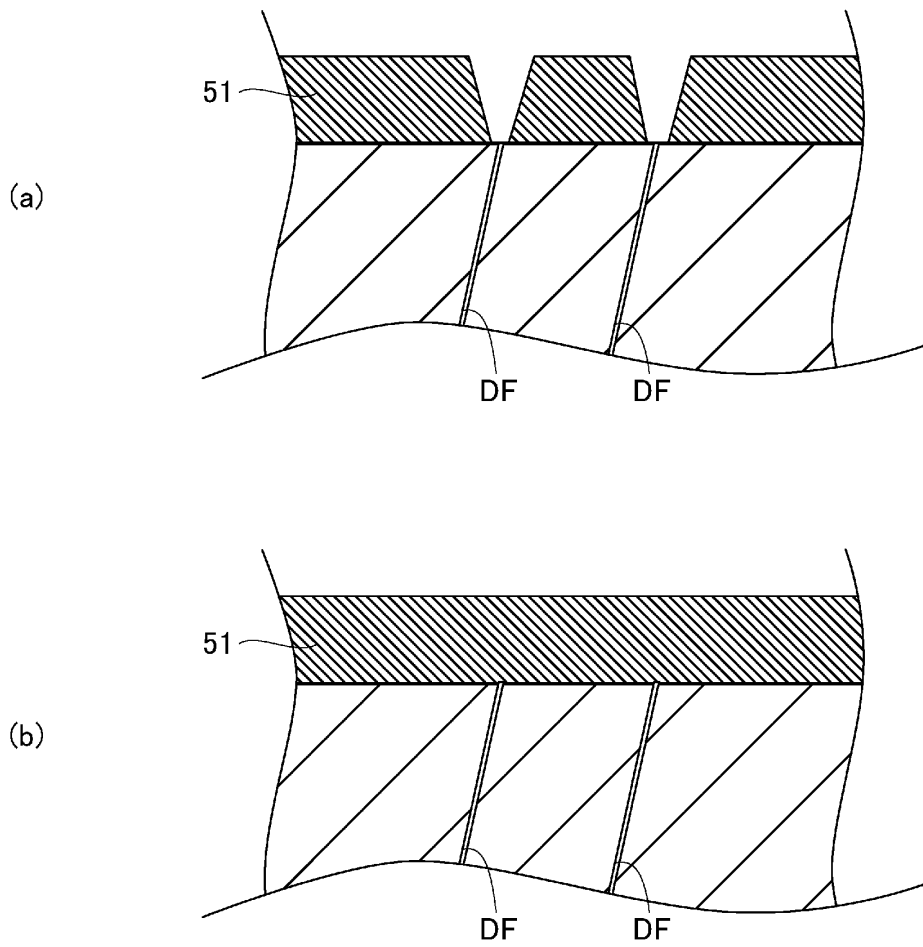
[図1]



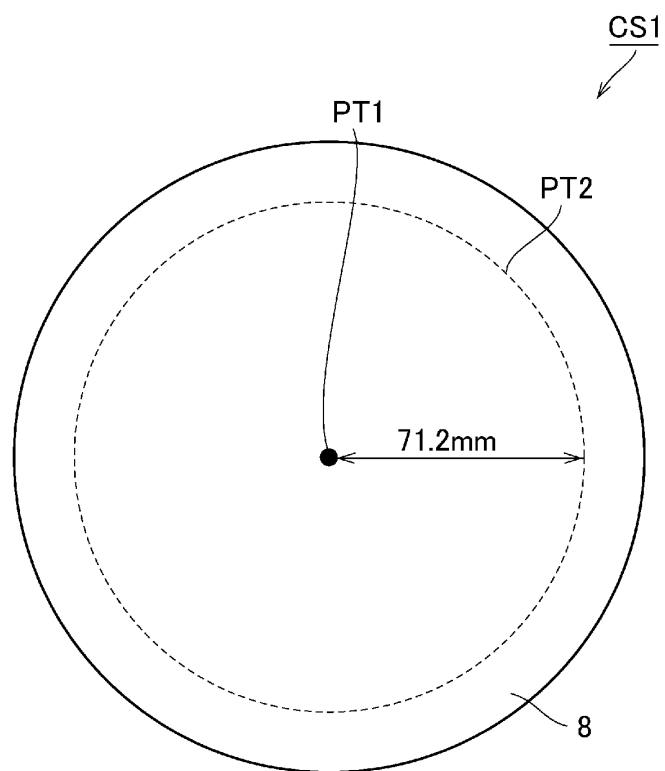
[図2]



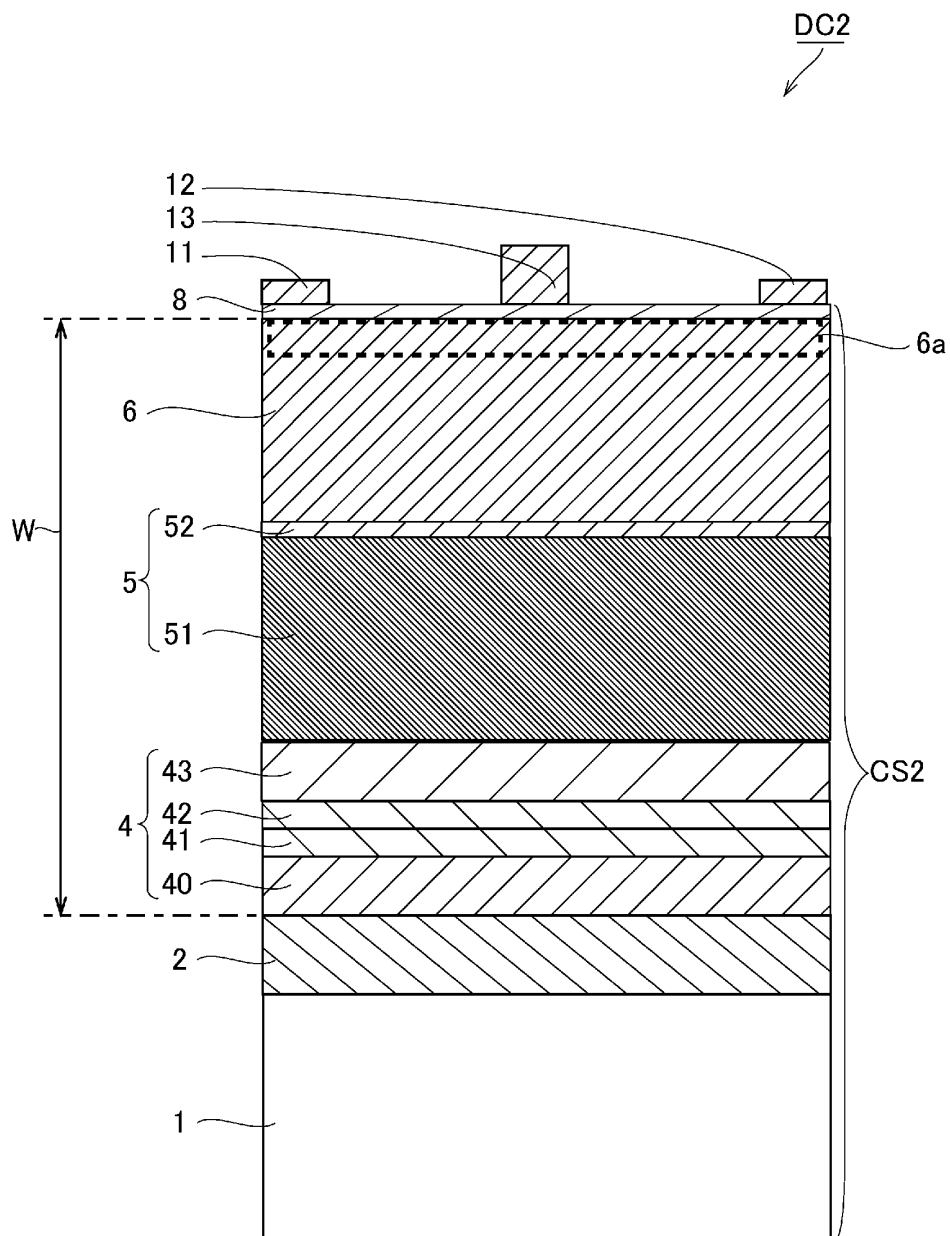
[図3]



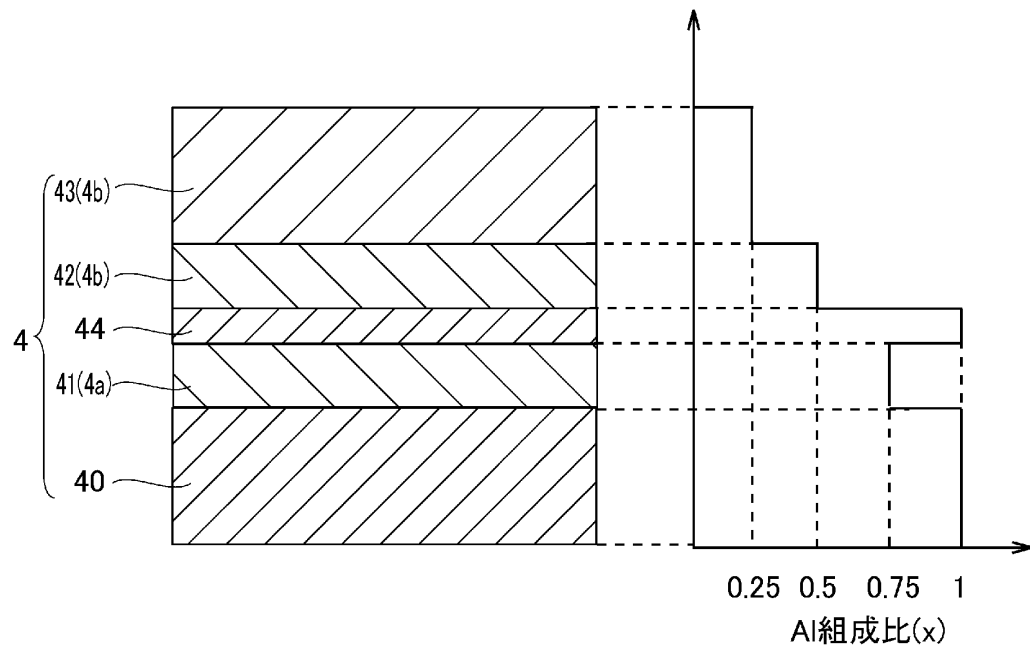
[図4]



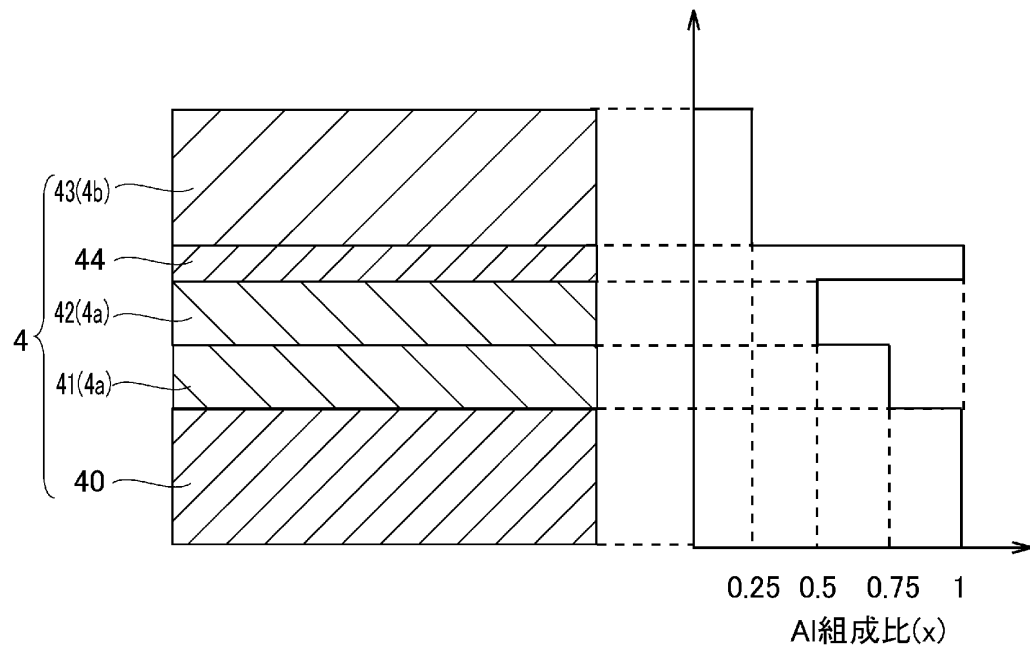
[図5]



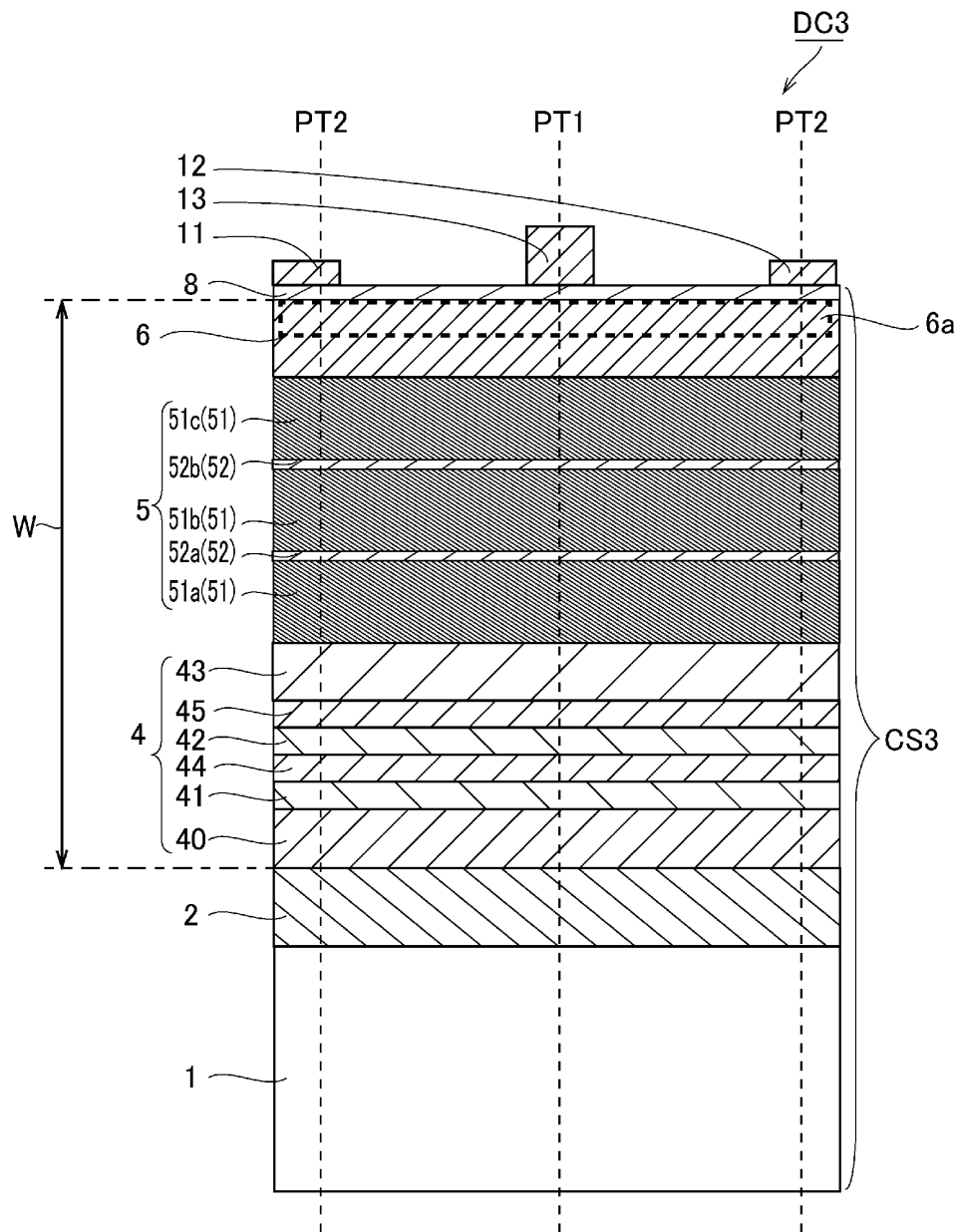
[図6]



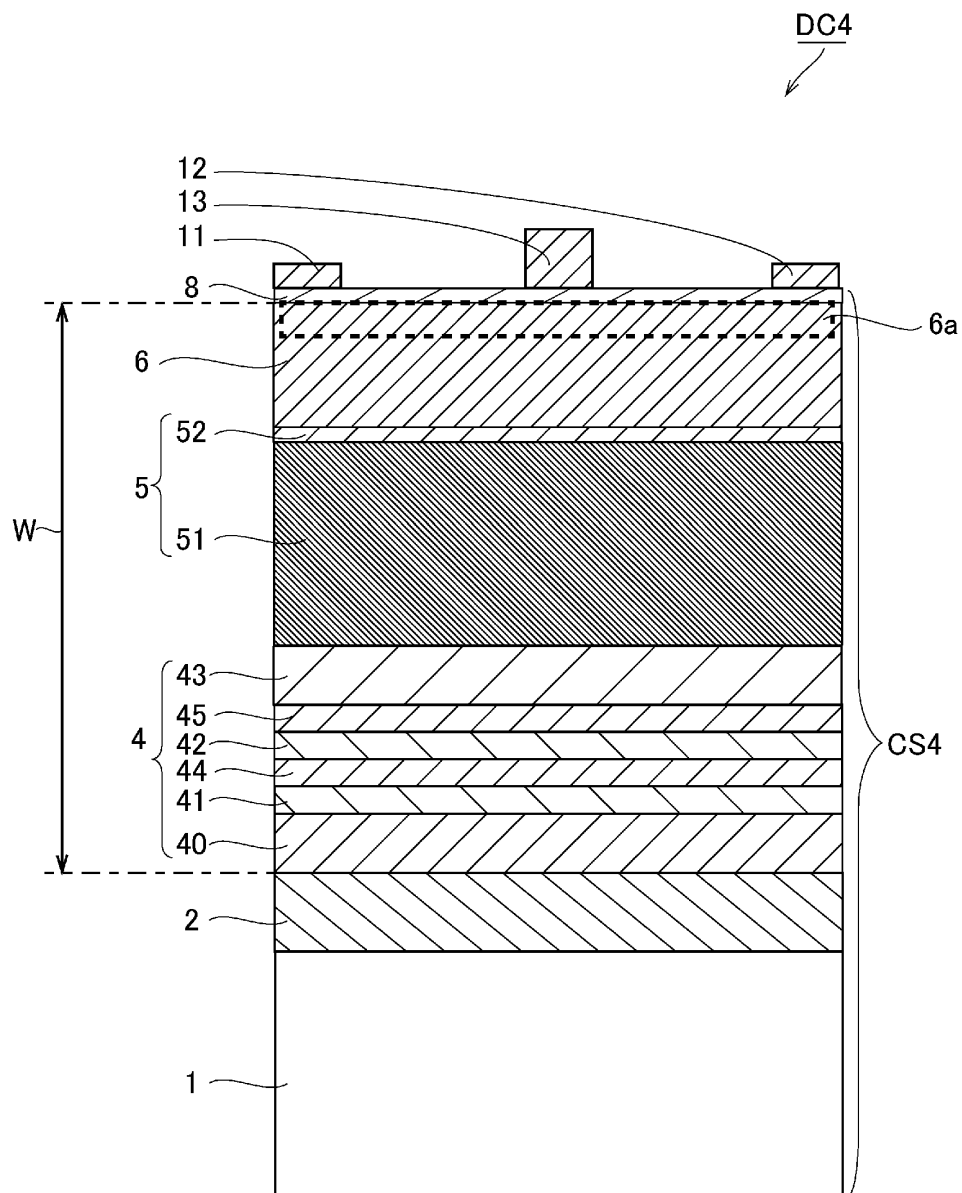
[図7]



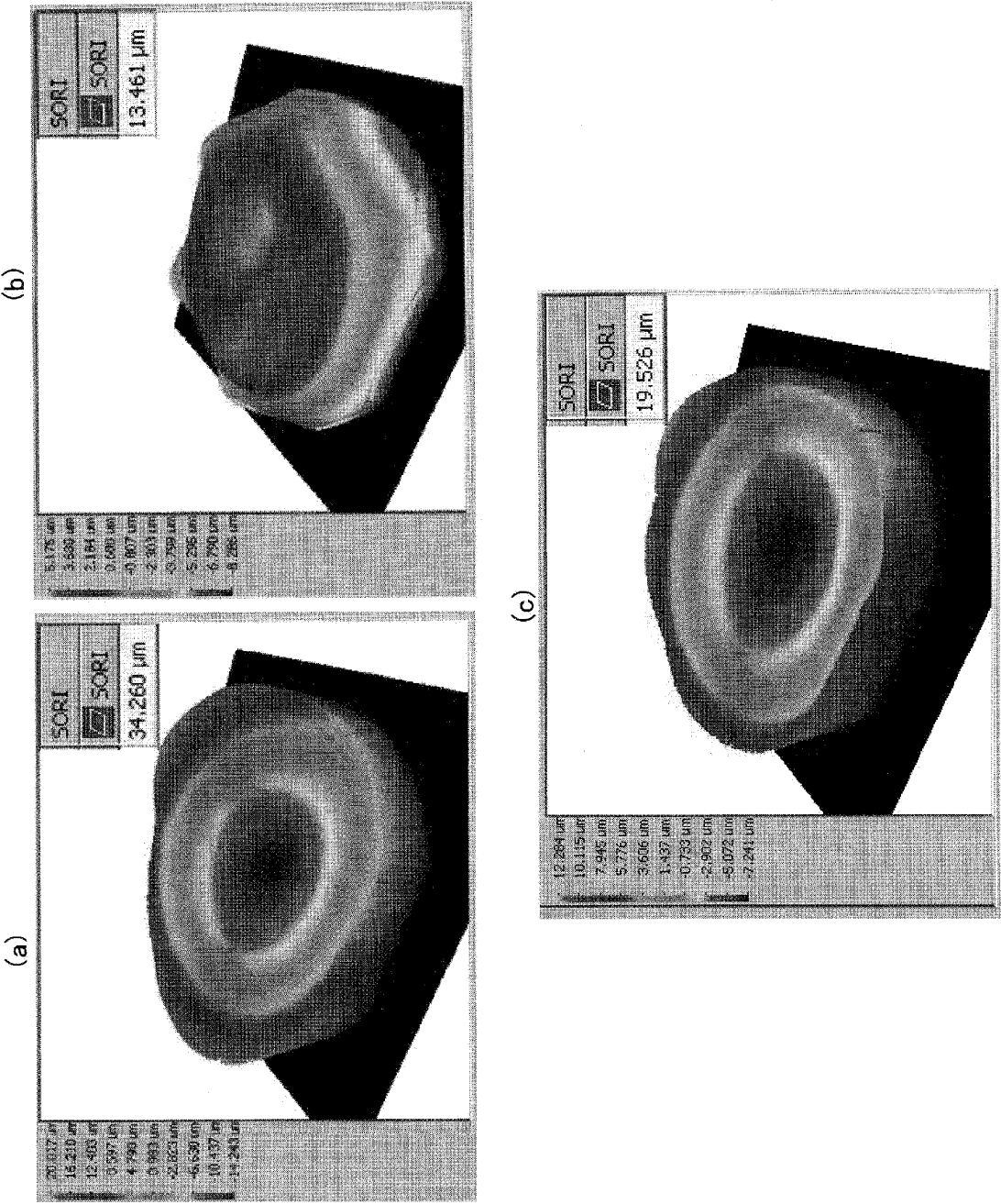
[図8]



[図9]

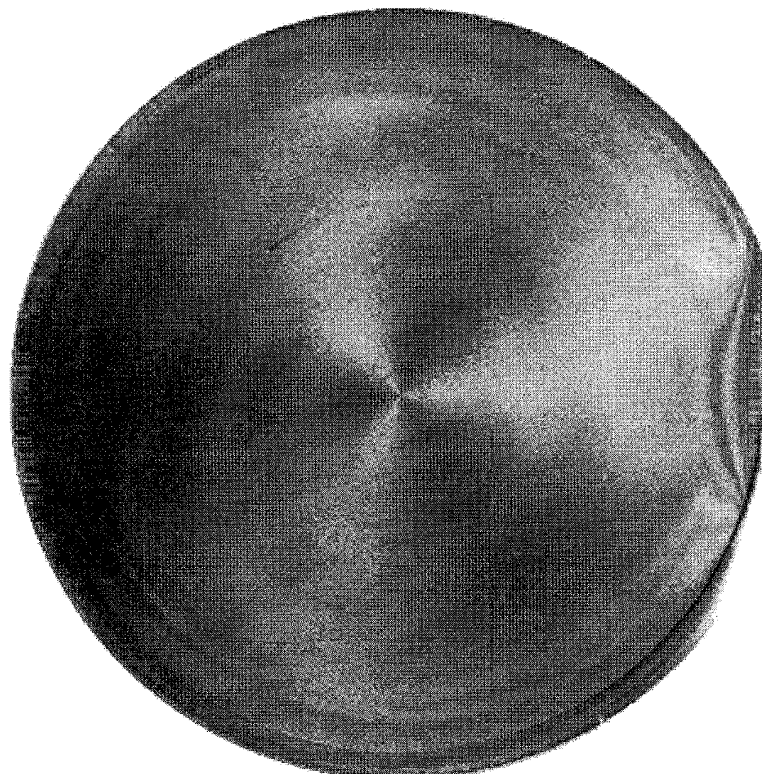


[図10]

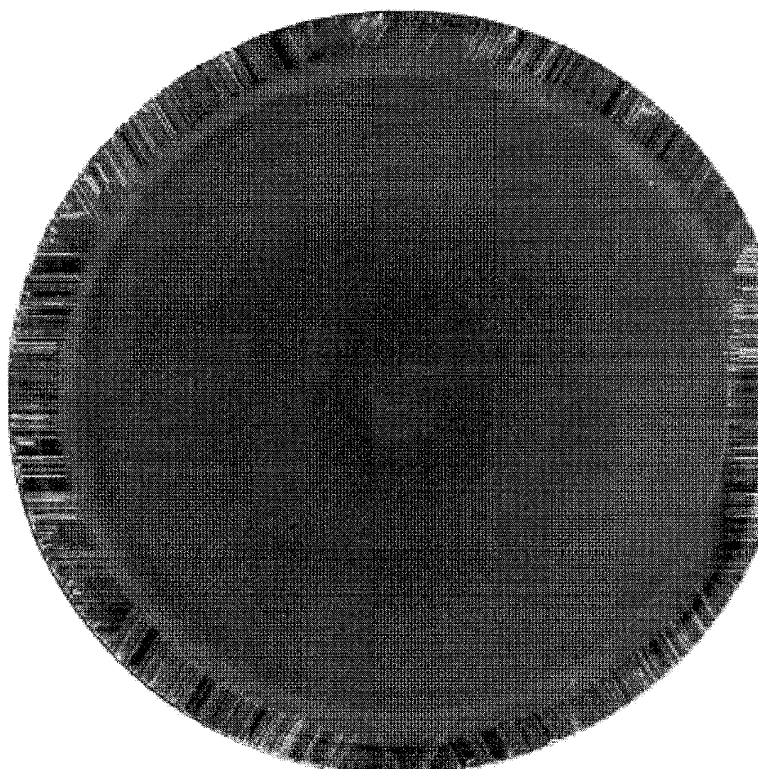


[図11]

(a)

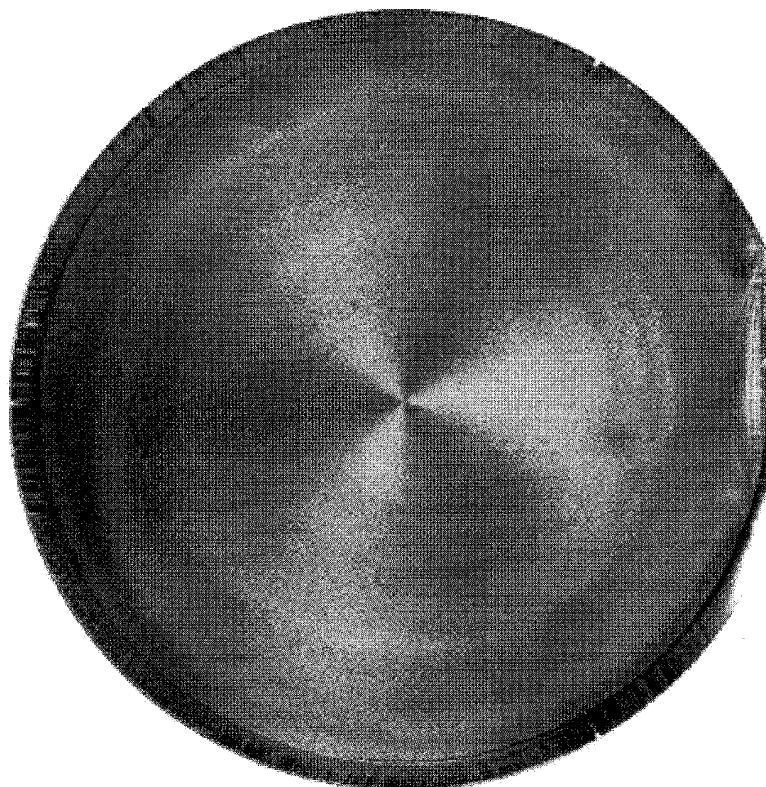


(b)

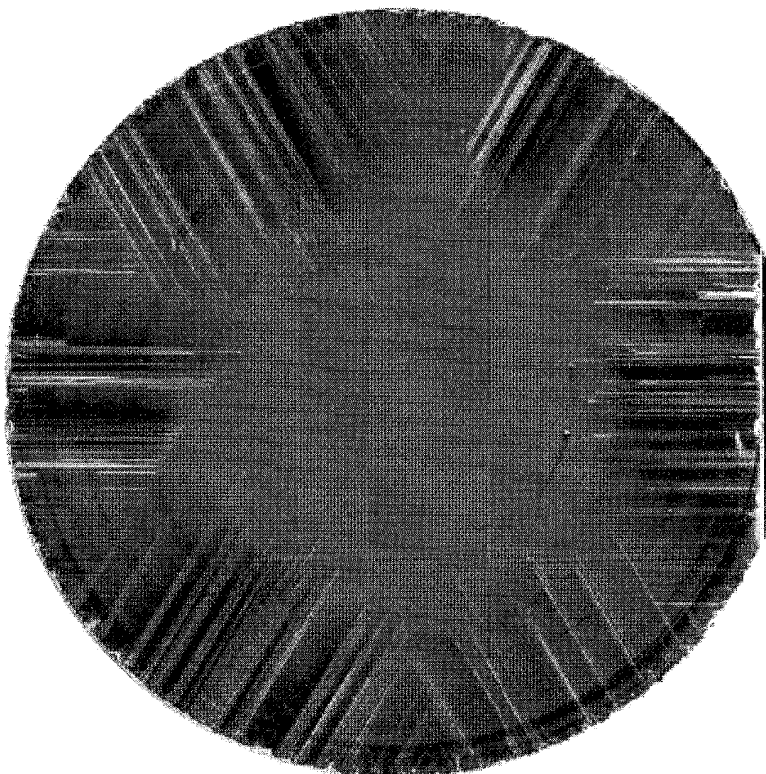


[図12]

(a)

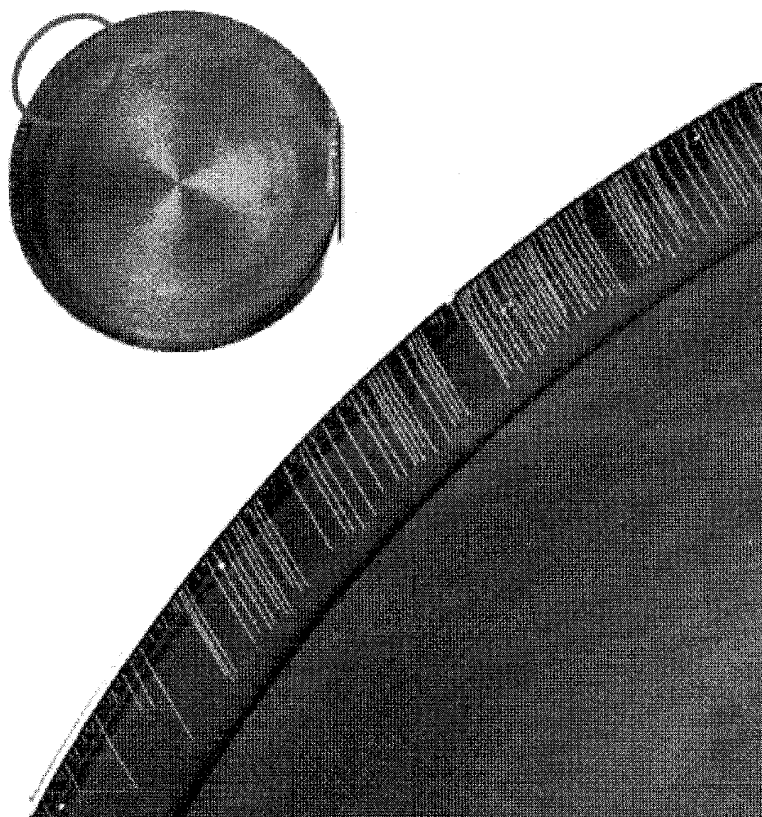


(b)

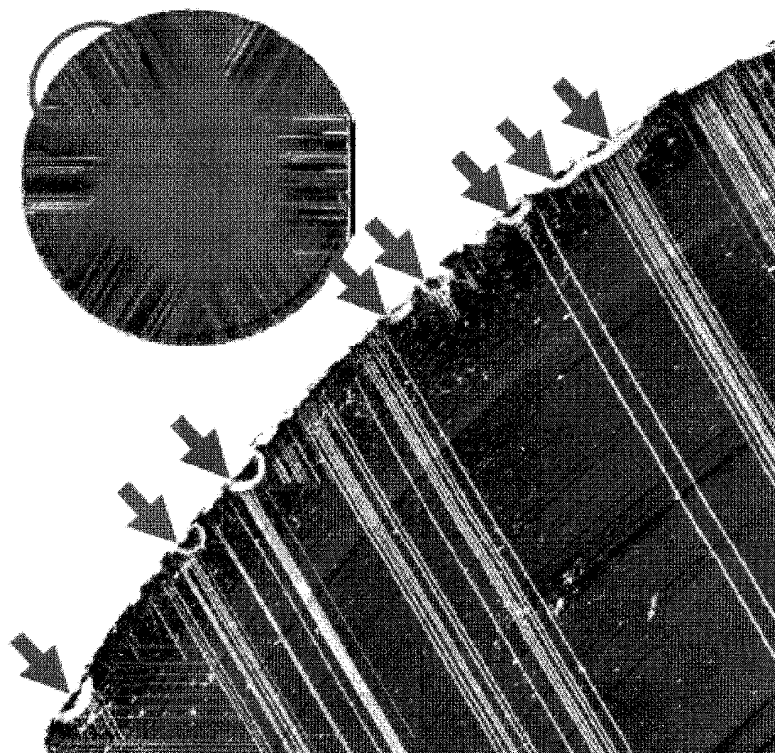


[図13]

(a)

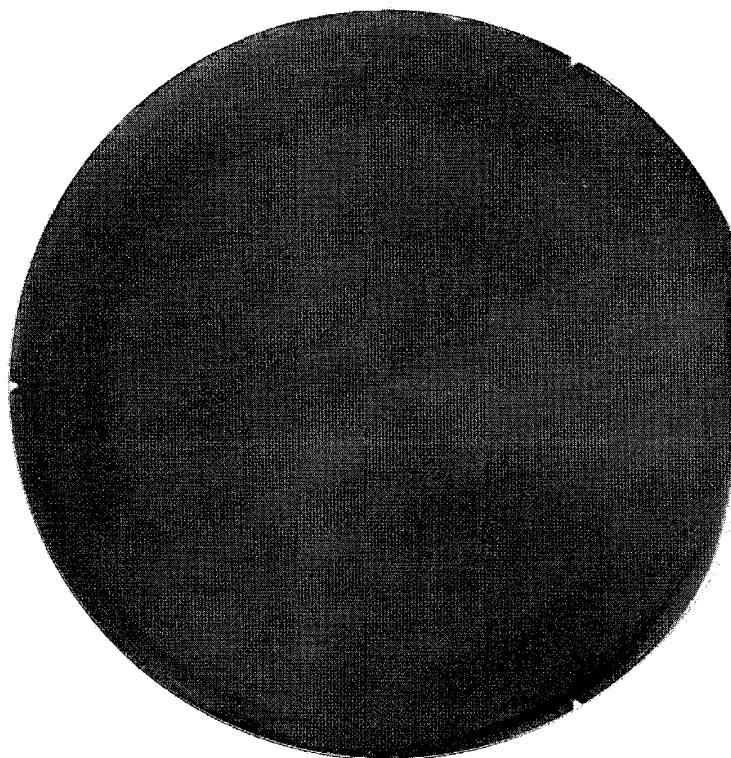


(b)

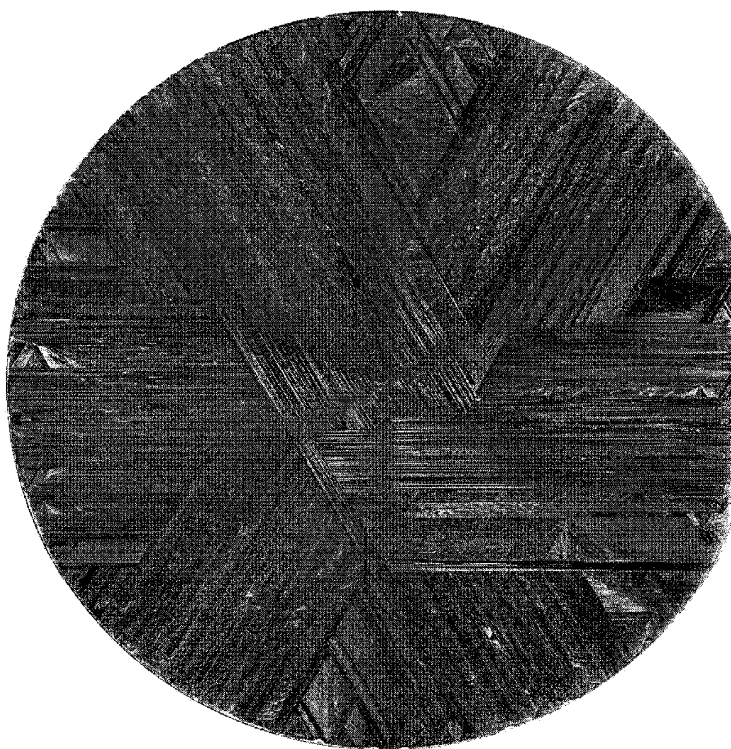


[図14]

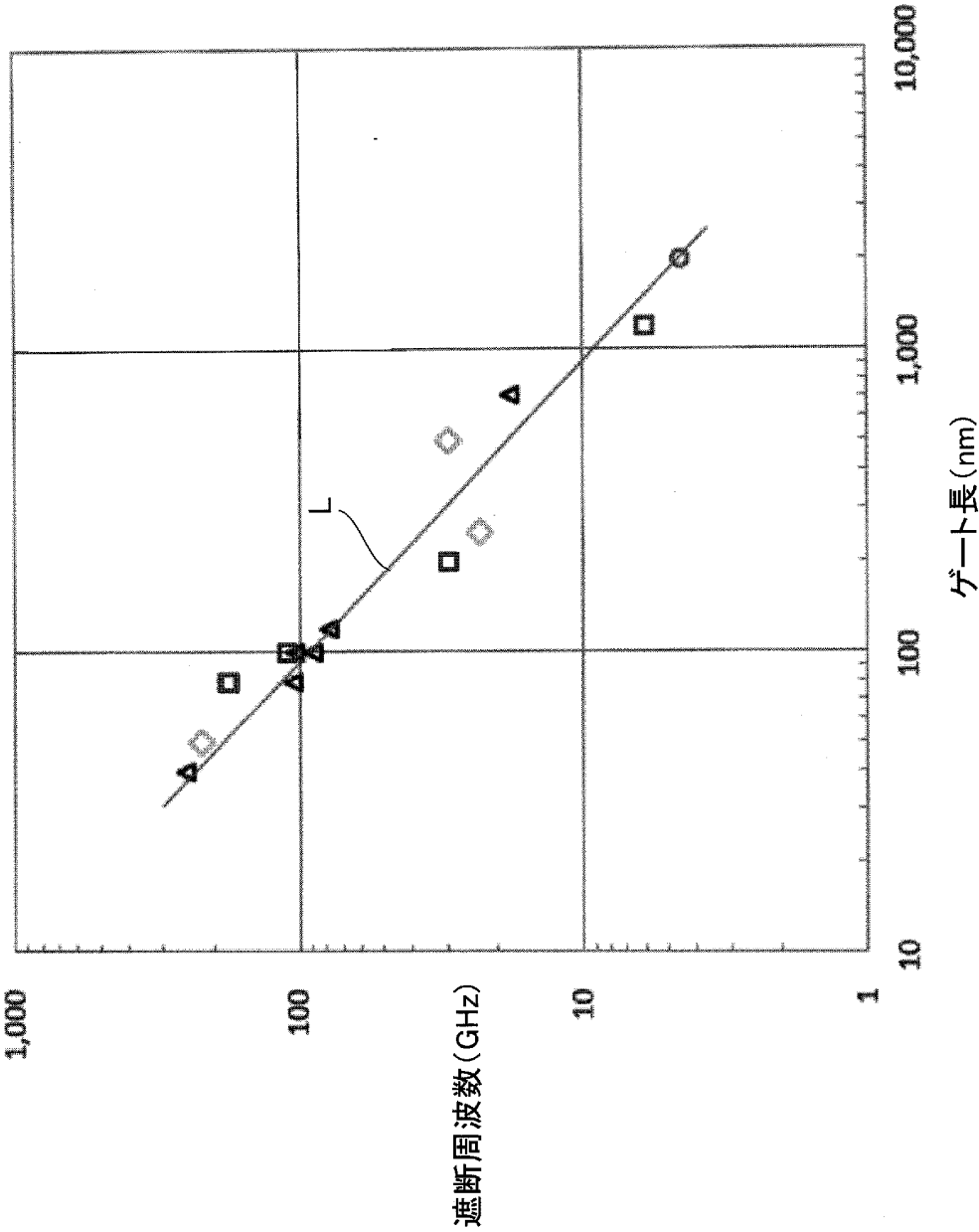
(a)



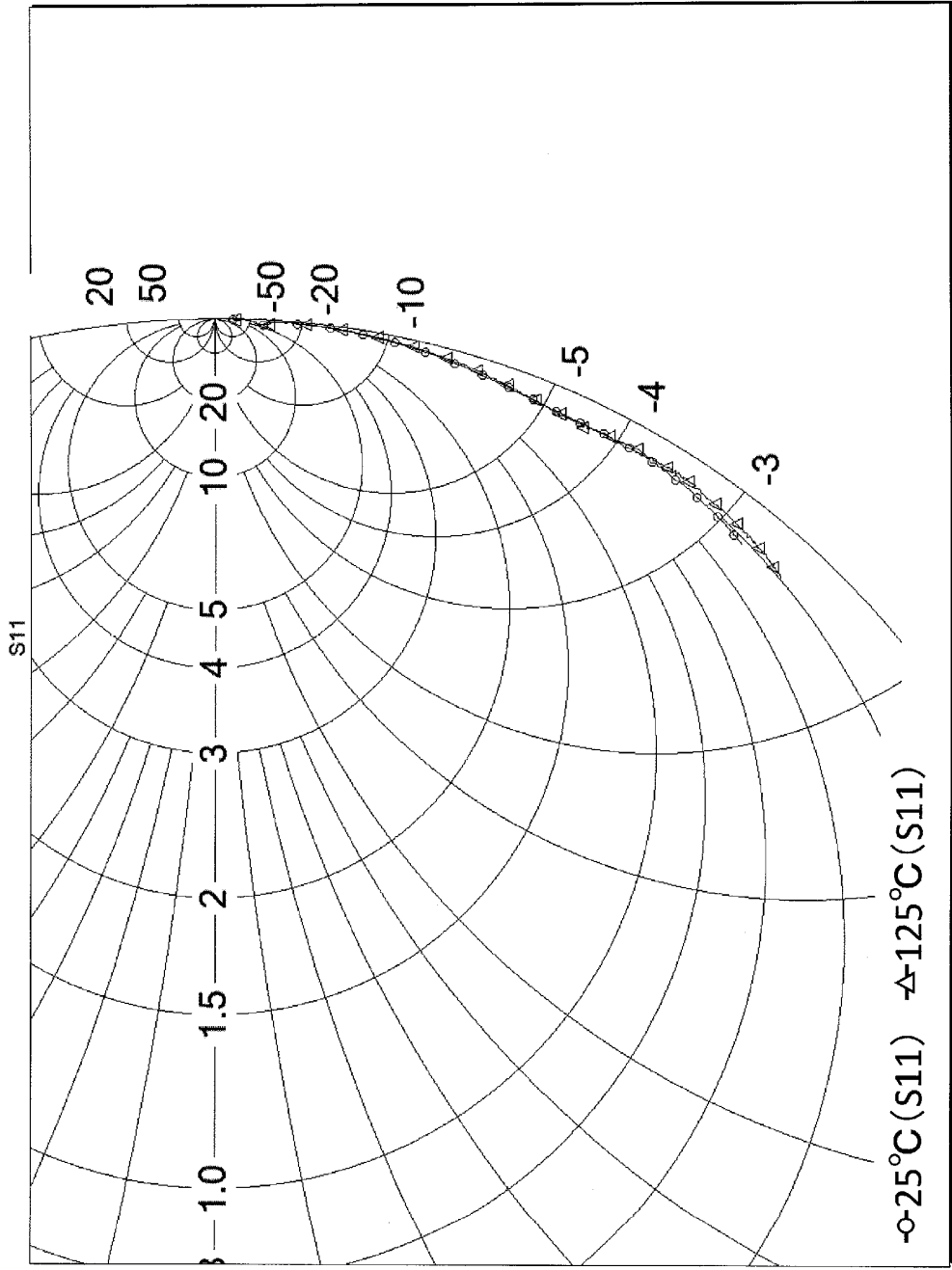
(b)



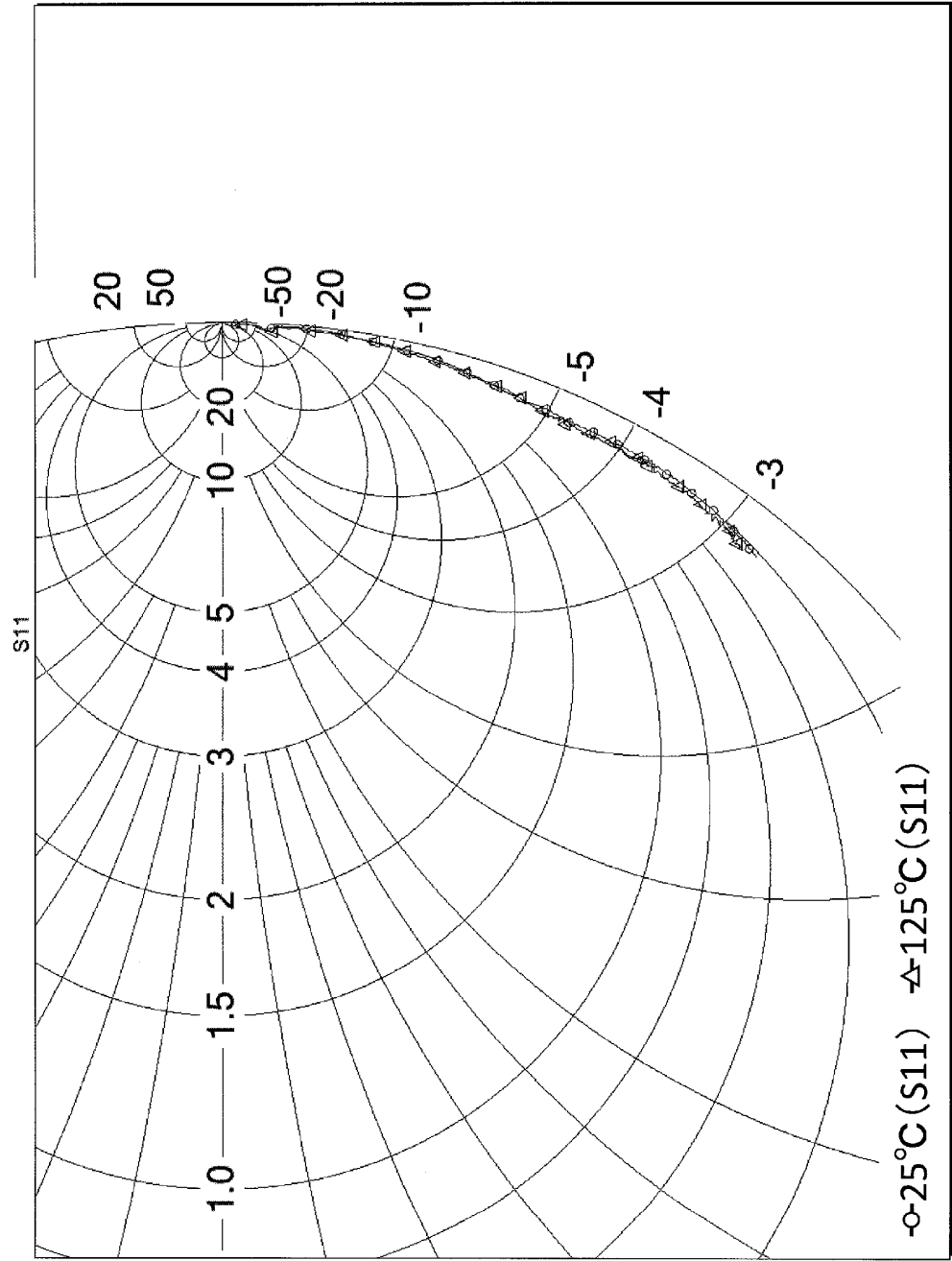
[図15]



[図16]



[図17]



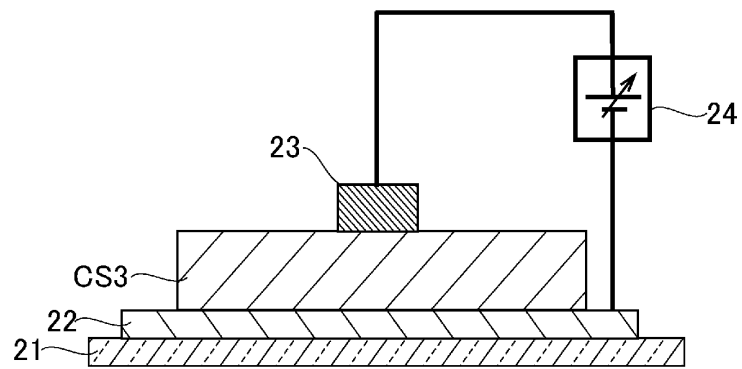
[図18]

試料	試料10	試料11
C-GaN層51cの 濃度誤差 ΔC	0%	258%
C-GaN層51bの 濃度誤差 ΔC	21%	312%
C-GaN層51aの 濃度誤差 ΔC	33%	448%

[図19]

試料	試料10	試料11
C-GaN層51cの 膜厚誤差 ΔW	1.2%	11%
C-GaN層51bの 膜厚誤差 ΔW	1.8%	11%
C-GaN層51aの 膜厚誤差 ΔW	3.9%	9%

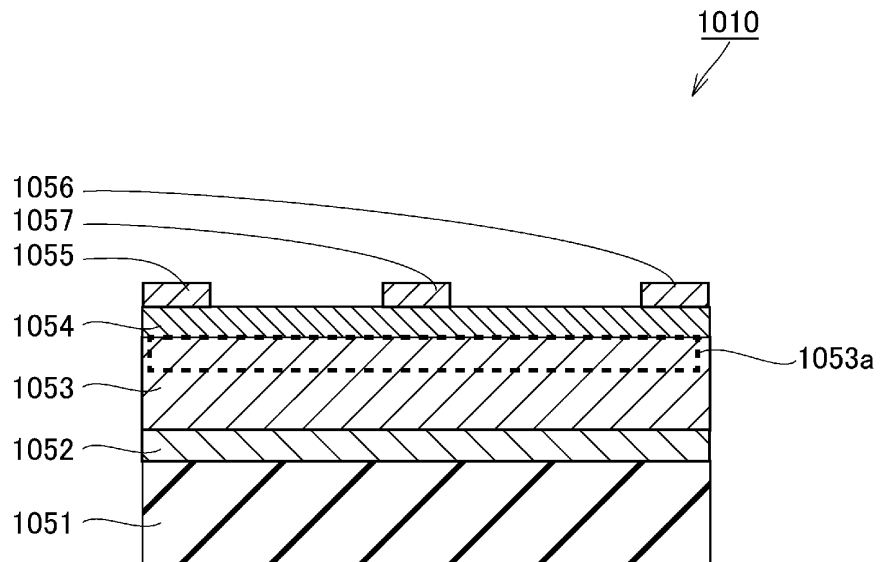
[図20]



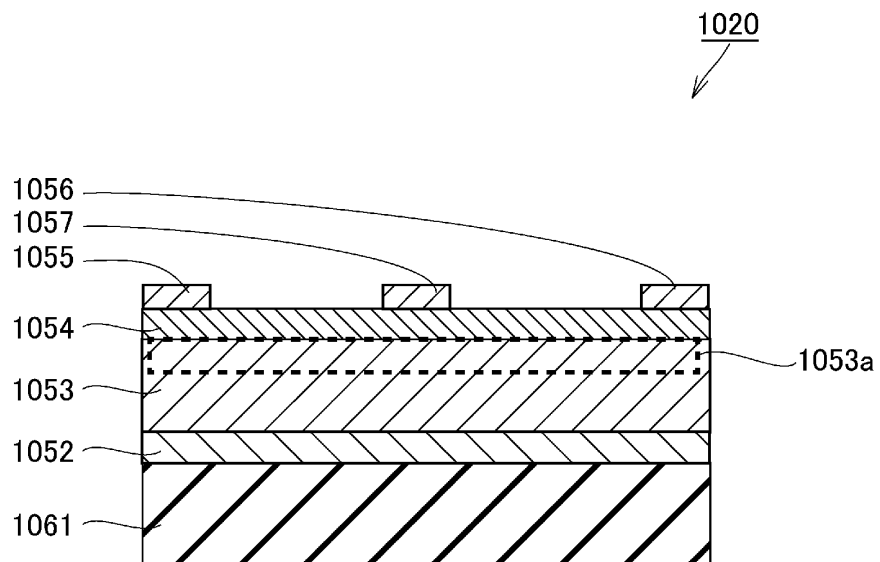
[図21]

試料	試料10		試料11	
位置	中心	エッジ	中心	エッジ
欠陥密度(個/cm ²)	1.8	1.8	207	7.1

[図22]



[図23]



[図24]

